

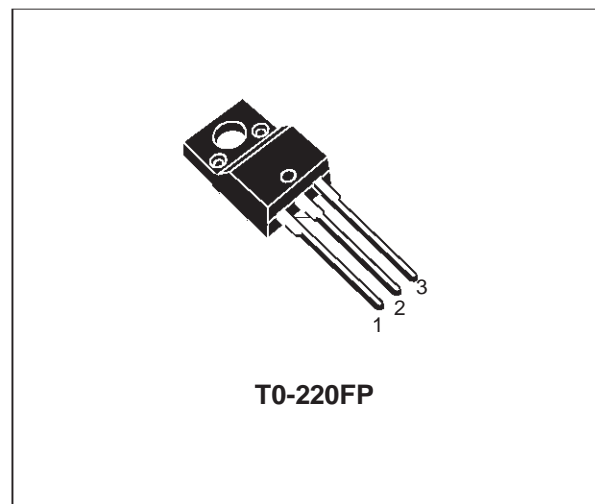
SILICON POWER DARLINGTON TRANSISTOR

APPLICATIONS:

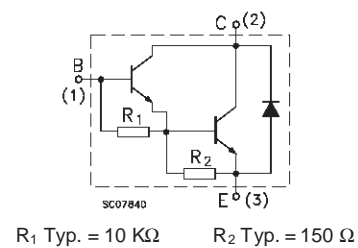
- GENERAL PURPOSE SWITCHING AND AMPLIFIER
- LINEAR AND SWITCHING INDUSTRIAL EQUIPMENT
- FULLY MOLDED ISOLATED PACKAGE
- 2000 V DC ISOLATION (U.L. COMPLIANT)

DESCRIPTION

The BDX53BFP is a silicon epitaxial-base NPN power transistor in monolithic Darlington configuration and are mounted in T0-220FP fully molded isolated package. It is intended for use in hammer drivers, audio amplifiers and other medium power linear and switching applications.



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage (I _E = 0)	80	V
V _{CEO}	Collector-Emitter Voltage (I _B = 0)	80	V
V _{EBO}	Emitter-base Voltage (I _C = 0)	5	V
I _C	Collector Current	8	A
I _{CM}	Collector Peak Current (repetitive)	12	A
I _B	Base Current	0.2	A
P _{tot}	Total Dissipation at T _c ≤ 25 °C	29	W
T _{stg}	Storage Temperature	-65 to 150	°C
T _j	Max. Operating Junction Temperature	150	°C

BDX53BFP

THERMAL DATA

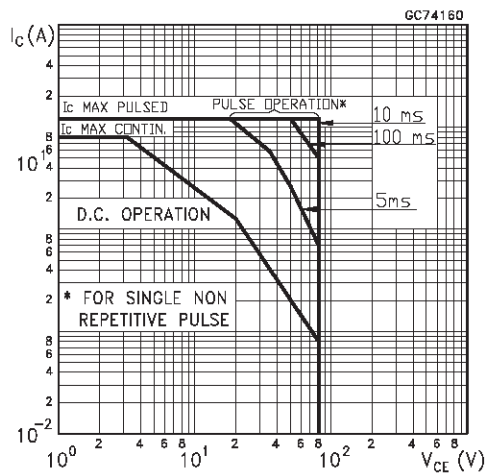
R _{thj-case}	Thermal Resistance Junction-case	Max	4.3	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	70	°C/W

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CBO}	Collector Cut-off Current (I _E = 0)	V _{CB} = 80 V			0.2	mA
I _{CEO}	Collector Cut-off Current (I _B = 0)	V _{CB} = 40 V			0.5	mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			2	mA
V _{CEO(sus)*}	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 100 mA	80			V
V _{CE(sat)*}	Collector-emitter Saturation Voltage	I _C = 3 A I _B = 12 mA			2	V
V _{BE(sat)*}	Base-emitter Saturation Voltage	I _C = 3 A I _B = 12 mA			2.5	V
h _{FE*}	DC Current Gain	I _C = 3 A V _{CE} = 3 V	750			
V _{F*}	Parallel-diode Forward Voltage	I _F = 3 A I _F = 8 A		1.8 2.5	2.5	V V

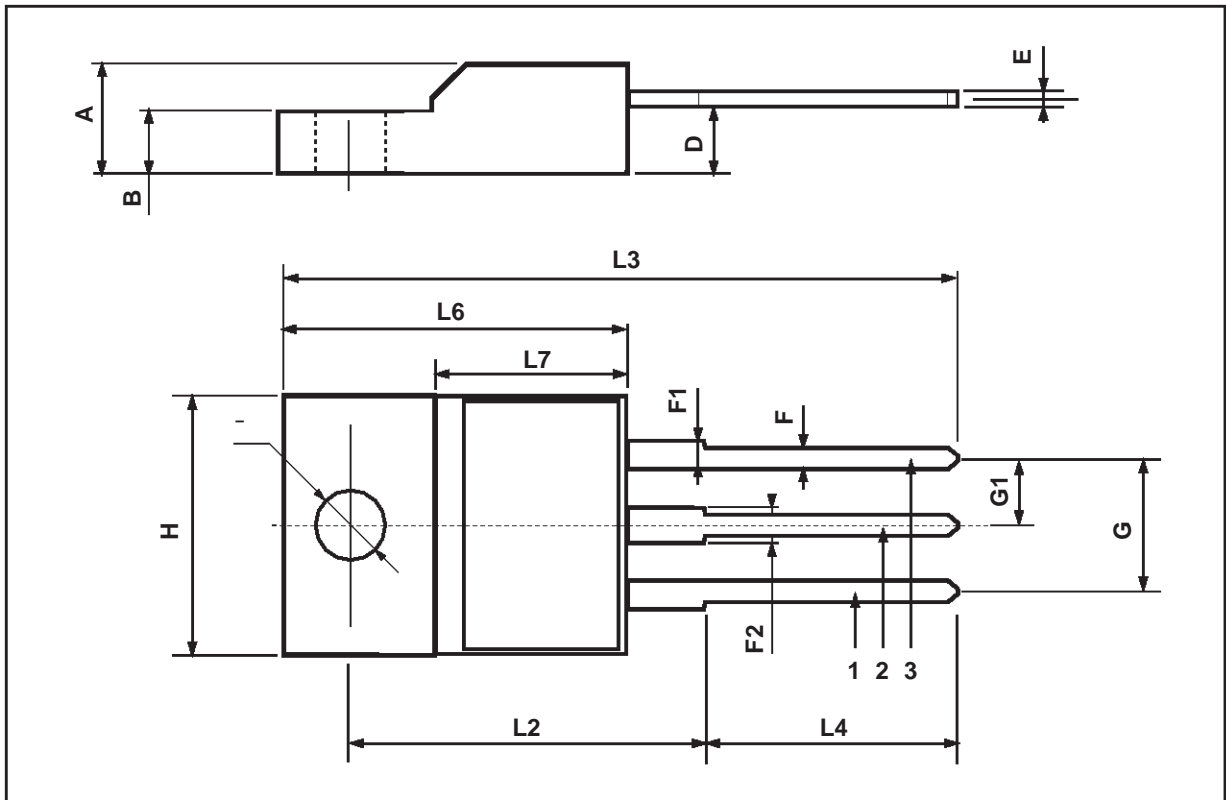
* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

Safe Operating Area



TO-220FP MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



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